AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method of forming a gate electrode in a semiconductor, comprising:

forming a polysilicon film and a ~~metal~~ tungsten silicide film sequentially on a semiconductor substrate, forming the tungsten silicide film by reacting SiH_4 or SiH_2Cl_2 with WF_6 at a stochiometric ratio of (SiH_2 or SiH_2Cl_2): WF_6 of 2.0 to 2.8;

performing an annealing process to crystallize the ~~metal~~ silicide film; and

forming a gate electrode by performing a single etching process on the ~~metal~~ tungsten silicide film and the polysilicon film.

2. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, wherein the annealing process is one of an rapid thermal process (RTP) annealing process and a furnace annealing process for crystallizing an amorphous ~~metal~~ tungsten silicide film to form a crystalline metal silicide film.

3. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 2, ~~wherein~~ comprising performing the RTP annealing process ~~is performed~~ at a temperature ranging from about 900°C to about 1000°C for a time period ranging from about 10 seconds to about 30 seconds in an ambient atmosphere of N_2 or NH_3 gas, and ~~wherein~~ performing the furnace annealing process ~~is performed~~ at a temperature ranging from about 850°C to about 1000°C for a time period ranging from about 5 minutes to about 30 minutes in an ambient of N_2 or NH_3 gas.

4. (Canceled)

5. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, ~~wherein~~ comprising performing the etching process ~~is performed~~ under a process condition for etching the polysilicon film.

6. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 5, wherein the etching process is a dry etching process ~~which is performed~~, and comprising performing the etching process in an inductively coupled plasma chamber into which a mixture gas of Cl_2 gas and O_2 gas is introduced.

7. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, wherein the etching process is a dry etching process ~~which is performed~~, and comprising performing the etching process in an inductively coupled plasma chamber into which a mixture gas of Cl_2 gas and O_2 gas is introduced.

8. (Original) The method of forming a gate electrode in a semiconductor according to claim 1, where in the annealing process results in the etch rate of the crystallized metal silicide film being similar to that of the polysilicon film